

ABSTRACT

A buffer layer of a light-emitting semiconductor device and the method of fabricating the same are disclosed. The method includes the steps of: providing a substrate, forming a metal layer on the substrate by supplying a organic metal
5 gas, and forming a metallic nitride layer by supplying a nitride gas to react with part or all of metal layer. The method is characterized in that the reaction gas is supplied separately and the buffer layer is formed with two steps or multiple steps in order to reduce the cleaning times and material waste, thereby realizing a cost-down and efficient manufacturing process.

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